L Number	HITS	Search Text	DB	Time stamp
4	10	(sic or silicon adj carbide) near2 seed same (boule or ingot) and 117/\$4.ccls.	USPAT; US-PGPUB;	2002/ <u>1</u> 1/26 10:55
			EPO; JPO; DERWENT;	13.03
5	39	(sic or silicon adj carbide) near2 seed	IBM_TDB USFAT;	2002 '11 '26
		same diameter	US-PGPUB; EPO; JPO;	11:22
			DEFWENT;	
6	9	(sid or silicon adj darbide) near2 seed and (gan or gallium adj nitride)	IBM_TDB USPAT; US-PGPUB;	2002/11/26 11:25
			EPO; JPO; DERWENT:	
8	14	(sic or silicon adj carbide) near2	IBM_TDB USPAT;	2002/11/26
		substrate and (gan or gallium adj	US-PGPUE;	11:30
		nitride) same (ingot or boule)	EPO; JPO; DERWENT; IBM TOB	
9	40	(sic or silicon adj carbide) near2 seed	USPAT;	2002/11/26
		and diamond	US-PGPUE; EPO; JPC;	11:31
			DERWENT; IBM TDB	
10	8	(sic or silicon adj carbide) near2 seed	USFAT:	2002/11/26
		same diamond	US-PGPUE; EPO; JPO;	11:31
			DEFWENT;	
	108	((pressure same (vary or varying or	IBM_TDB USFAT;	2002/10 21
		varied or varing or alternated or	US-PGFUB;	09:44
		alternating or alternate)) and (sic or silicon adj carbide)) and (117/\$4.ccls. or 427/\$4.ccls.) and (carbon or silicon)	EPO; JPO; DEPWENT; IBM_TDB	
	9.4	<pre>near3 source ((sic or silicon adj carbide) and</pre>	USPAT;	: 2002/10/21
	0 4	117/84-109.ccls.) and source and cycle	US-PGPUB;	10:01
			EPO; JPO; DEPWENT;	
	55	((sic or silicon adj carbide) and	IBM_TDB USPAT;	2002,10/21
		117/84-109.ccls.) and puls\$4	US-PGFUB;	11:19
			PEPO; JPO; DEPWENT;	
	ΕA	(partial adj pressure) same (silicon or	IBM_TIB USPAT;	2002/10/21
	24	carbon or si or c) and (sic or silicon	US-PGFUE;	14:33
		adj carbide) and 117/84-109.ccls.	EPO; JPC;	
			DEFWENT;	
	38	(partial adj pressure) same (silicon or	USFAT;	2002/10, 21
		carbon) and (sic or silicon adj carbide)	US-PGFUE;	15:45
		and 117/84-109.ccls.	EPO; JPO; DEPWENT; IBM TDB	
	28	(sic or silicon adj carbide) same (npn or	USFAT;	2002/10/21
		pnp) and (438/\$4.ccls. or 117/\$4.ccls.)	EPO; JPO;	15:19
			DEFWENT; IBM TLB	
		sccm near10 (silicon or carbon) and (sic	USFĀT;	2002/10/21
		or silicon adj carbide) and 117/84-109.ccls.	US-PGPUB; EPC; JPO; DERWENT;	15:54
			IBM TDB	

	907	(sic or silicon adj carbide) near3 seed and 117/84-139.ccls.	USPAT; US-PGPUB; EPO; JFO;	2002710721 16:02
			DEFWENT;	
_	13	attach\$4 near3 coefficient and	IBM_TDB USFAT;	2002 (10 (22
	13	117/84-109.ccls.	US-PGFUB; EFO; JFO;	09:35
			DEFWENT;	
_	5.4	((sic or silicon adj carbide) and	IBM_TDE USPAT;	2002 '10 '21
	•	117/84-109.ccls.) and flow adj rate same	US-PGFUE;	17:39
		(silicon or carbon) same (carbide or sic)	EPO; JPO; DERWENT;	
			IBM_TIB	
=	3 /	attach\$4 near3 coefficient and (silicon	USPAT;	2002-10,22
		adj carbide or sic)	US-PGFUB; EPO; JPD;	09:54
			DERWENT:	
-	9	attach\$4 adj coefficient and (silicon adj	USPAT;	2702 10 22
		carbide or sic)	US-PGFUB;	11:5.
			EPO; JPD;	
			DERWENT; IBM TDB	
_	18	superlattice same (sic or silicon adj	USFAT;	2002/10/22
		carbide) same dop\$4	US-PGPUB;	13:36
			EPO; JPO;	
			I-ERWENT;	
_	1.6	superlattice same (sic or silicon adj	IBM_TDE USFAT;	2:02:10 /22
	10	carbide) and cycle		15:04
			EPO; JPO;	
			DEPWENT;	
	0.0	·	IBM_TIE	0.000 / 1.1 / 0.1
. –	, 80	<pre>superlattice same (silicon adj carbide or sic)</pre>		: 2002/11/21 : 17:46
		, 5107	EPO; JPO;	11.17
			DEFWENT;	
	1.0		IBM_TDE	2002/11/22
-	46	<pre>(ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4)) same (sic or</pre>	USFAT; US-PGFUB;	2002/11/22 09:40
		silicon adj carbide)	EPO; JPO;	
			LEPWENT;	
			IBM_TLB	07.00 /11 /00
-	38	<pre>attachment near2 coefficient same (gas\$4 or pressure)</pre>	USPAT; US-PGPUE;	2002/11/22 10:01
		or pressure,	EPO; JPO;	***************************************
			L'EFWENT;	
	4.2		IBM_TDB	0600:11,00
-	11	attachment near2 coefficient and (silicon adi carbide or sic)	USFAT; US-PGPUE;	2002:11:22 10:05
		adj Calbide of Sic/	EP0; JP0;	± € + W ↔
			DEFWENT;	
			IBM_TDB	2602/11 22
_		attachment near2 coefficient same (silicon adj carbide or sic)	USFAT; US-PGPUB;	2002/11/22 10:13
		(SITICON adj Carbide of SIC)	EPC; JPO;	10.12
			DERWENT;	
			IBM_TDB	6666 55 55
-	20	((constant\$4 or stead\$4) near3 (gas or	USPAT;	2002,11,22 11:06
		reactant or pressure or flow) same (sic or silicon adj carbide)) and puls\$4	US-PGPUE; EPO; JPC;	11.00
		of Siffoon adj carpracy, and pursy:	DERWENT;	
			IBM_TIB	
-	17	117'84-109.ccls. and (silicon adj carbide		2002, 11, 22
		or sic) and puls\$4 near3 deposit\$4	US-PGPUB; EPO; JPO;	11:11
			CERWENT;	
			_IBM_TDB	

	11	117/84-109.zcls. and puls\$4 near3 deposit\$4 not laser	USPAT; US-PGPUB; EFD; JFO; DERWENT;	2002/11/22 11:53
-	22	(Sic or silicon adj carbide) same (vapor adj deposit\$4) same puls\$4	IBM_TDB USPAT; US-PGFUB; EFO; JFO; DERWENT; IBM TDB	2002/11/22 13:14
-	19	(vapor adj deposit\$4) near2 puls\$4 and (constant\$4 or continuous\$4 or stead\$4) near4 (flow\$4 or gas\$4 or react\$4)	USFĀT; US-PGFUB; EFO; JFO; DERWENT;	2002 11/22 13:25
-	7	(vapor adj deposit\$4) near2 puls\$4 and 117/84-109.ccls.	IEM_TIP USFAT; US-PGPUB; EPO; JFO; DEPWENT;	2002/11 '22 13:27
-	3	<pre>puls\$4 same (silicon adj carbide or sic) not laser and 117/84-109.ccls.</pre>	IEM_TIB USFAT; US-PGFUE; EPG; JPG; DEPWENT;	2002:11 22 13:34
-	17	<pre>puls\$4 near3 (deposit\$4 or growth) and superlattice and 117/84-109.ccls.</pre>	IBM_TDB USFAT; US-PGPUF; EPG; UPG; DEFWENT; IBM TDB	2002:11 22 13:4°
-	14	<pre>puls\$4 near3 (deposit\$4 or growth) and superlattice not laser</pre>	USFAT; US-PGPUB; EPC; CPO; DEFWENT; IBM TDB	2002/11/22 19:29
-	13	<pre>puls\$4 near3 (reactant) and (stead\$4 or continuos\$4 or constant\$4) near3 (reactant)</pre>	·	2002/11/25 10:45
-	6	<pre>(si or silicon) near2 (sic or silicon adj carbide) same superlattice</pre>	USFAT; US-PGPUB; EPO; JPO; DEPWENT; IBM TDB	2002/11/22 15:16
-		<pre>(si or silicon) near2 (sic or silicon adj carbide) and (((si or silicon) near3 (reactant or source or gas) and (carbon) near2 (reactant or source)) same (puls\$4 or continuous\$4 or stead\$4))</pre>	USFAT; US-PGFUB; EPO; JPO; DEPWENT; IBM TDB	2002,11/22 15:24
-	36		USFAT; US-PGFUB; EPG; UPO; DEPWENT; IBM TDB	2002/11/22 15:36
-	10	puls\$4 near3 deposition same superlattice	USFAT; US-PGPUB; EPO; JPO; LERWENT; IBM TIB	2002/11/22 15:39
-	7	puls\$4 near3 deposition and superlattice not laser	USFAT; US-PGPUB; EPG; GPC; DEPWENT; IBM TIB	2002/11/22 15:41
_	6	superlattice same (silicon or si) near2 (silicon adj carbide or sic)	USFAT; US-PGFUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 15:44

· _ ·	 5 1	(silicon adj carbide or sic) same puls\$4	USPAT;	~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	
-		same deposit\$4 not laser	US-PGPUB; EPO; JPO;	16:13	
			DERWENT; IEM TDB		
	32	(silicon adj carbide or sic) same	USPAT;	2002 111 122	
		(deposit\$4) and (silicon or si) near3	US-PGFUB;	16:14	
		(partial adj pressure)	EPO; JPO;		
			DERWENT; IBM TDB		
-	3	((carbon or silicon or si) near2 (stead\$4	USPAT:	2002 11/25	
		or continuos\$4 or constant\$4) near2 (flow		11:10	
		or pressure)) and (sic or silicon adj	EPO; JPO;		
		carbide	LERWENT; IBM TIB		
-	9	(silicon adj carbide or sic) same (vapor	USFAT;	2002.11 25	
		adj phase adj epitaxy or sulimation adj	US-PGFUB;	13:47	
		recrystallization or liquid adj deposition) same bulk	EPC; JPO;		
		deposition; same bulk	DEPWENT; IBM TDB		
-	9	(silicon adj carbide or sic) adj bulk and	USFAT;	2002,11 25	
		(vapor adj phase adj epitaxy or	US-PGlUB;	13:51	
		sulimation adj recrystallization or liquid adj deposition)	EPO; JPO; LERWENT;		
		inquid adj deposition;	IBM TLB		
-	92	(silicon adj carbide or sic) same (low	USPAT;	2002/11 25	
		adj pressure same CVD)	US-PGFUE;	13:57	
			EPG; JPG; LEPWENT;		
			IBM TIB		
_	14	(silicon adj carbide or sic) same (low	USFĀT;	2002,11.25	
		adj pressure same CVD) and growth adj	US-PGFUP;	14:28	
		rate	EPO; JPC; DEPWENT;		
			IBM TLB		
-		(silicon adj carbide or sic) same (CVD) and growth adj rate same (sic or silicon adj carbide)	USPAT;	2002/11/25	
			US-PGPUB; EPO; JPO;	14:40	
		ady Calbide;	LEFWENT;	1	
			IBM_TDB		
_	35	(CVD) same growth adj rate same (sic or	USFAT; US-PGFUE;	2002/11/25 15:04	
		silicon adj carbide)	EPO; JPO;	10.04	
			LEFWENT;		
			IBM_TIB	0.660 11/05	
-	Ĉ,	(sic or silicon adj carbide) near2 seed same (gan or gallium adj nitride or	USFAT; US-PGFUE;	2002/11/25 15:09	
		diamond)	EPO; JPO;	2000	
			DEFWENT;		
	_	(.iilimam adi gambida) mang gard	IBM_TDB USFAT;	2002/11/25	
-		(sic or silicon adj carbide) near2 seed and (gan or gallium adj nitride or	US-PGFUE;	15:24	
		diamond) same CVD	EPO; JPO;		
			DEFWENT;		
	1 Ć.	dop\$4 same superlattice same (sic or	IBM_TDB USFAT;	2002/11/25	
=	15	silicon adj carbide)	US-PGFUB;	17:09	
			EPO; JPO;		
			DEFWENT;		
			IBM_TDB		